

## 20V, 4.2mΩ, 60A, Single N-Channel

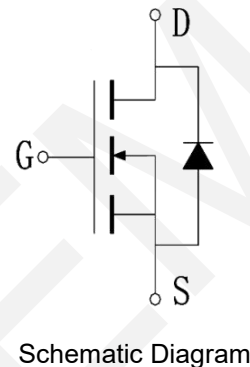
### 1.Features

- ◆ 20V MOSFET technology
- ◆ Low on-state resistance
- ◆ Fast switching
- ◆  $V_{GS} \pm 12V$

$V_{DS}$	$R_{DS(on)}$ Typ.	$I_D$ Max.
20V	4.2mΩ @ 7.4V	60A
	4.7mΩ @ 4.5V	
	7.5mΩ @ 2.5V	

### 2.Applications

- ◆ Power Switching Application
- ◆ Load Switching



### 3.Absolute Max Ratings at $T_a=25^\circ C$ (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	$V_{DSS}$	20	V
Gate to Source Voltage	$V_{GSS}$	$\pm 12$	V
Drain Current (DC)	$I_D$	60	A
Drain Current (Pulse), $PW \leq 300\mu s$	$I_{DP}$	162	A
Total Dissipation	$P_D$	62	W
Avalanche Energy, Single Pulsed	$E_{AS}$	156	mJ
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ C$

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### 4.Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to case	$R_{\theta JC}$	2.1	$^\circ C/W$

Note 2: When mounted on 1 inch square copper board  $t \leq 10$ sec The value in any given application depends on the user's specific board design.

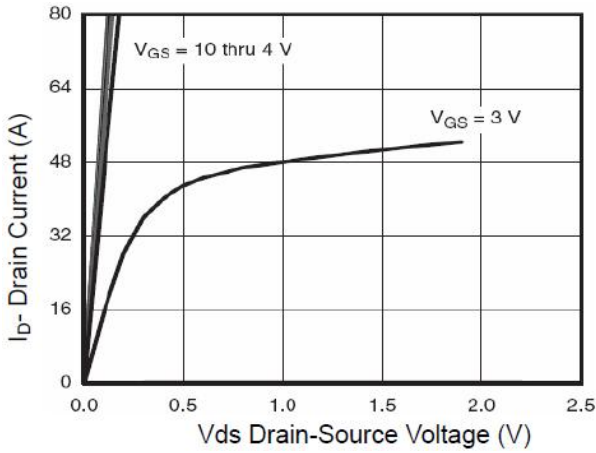
**5. Electrical Characteristics at Ta=25°C (Note 3)**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu A, V_{GS} = 0V$	20			V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 18V, V_{GS} = 0V$			1	$\mu A$
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0V$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	0.5	0.7	1.2	V
Static Drain to Source On-State Resistance	$R_{DS(on)}$	$I_D = 20A, V_{GS} = 7.4V$	-	4.2	5.4	m $\Omega$
		$I_D = 10A, V_{GS} = 4.5V$	-	4.7	6	m $\Omega$
		$I_D = 5A, V_{GS} = 2.5V$	-	7.5	12	m $\Omega$
Forward Transconductance	$G_{FS}$	$I_D = 20A, V_{DS} = 10V$	15			S
Input Capacitance	$C_{iss}$	$V_{GS}=0V,$		3042		pF
Output Capacitance	$C_{oss}$	$V_{DS}=10V,$		1569		pF
Reverse Transfer Capacitance	$C_{rss}$	Frequency=1.0MHz		1416		pF
Turn-ON Delay Time	$t_{d(on)}$	$V_{DD} = 10V, I_D = 2A,$ $V_{GS} = 4.5V,$ $R_G = 3\Omega, R_L=1\Omega$		6.4		ns
Rise Time	$t_r$			17.2		ns
Turn-OFF Delay Time	$t_{d(off)}$			29.6		ns
Fall Time	$t_f$			16.8		ns
Total Gate Charge	$Q_g$		$V_{DS} = 10V,$		35	
	$Q_{gs}$	$V_{GS} = 4.5V,$		3		nC
	$Q_{gd}$	$I_D = 20A$		10		nC
Diode Forward Voltage	$V_{FSD}$	$I_S = 20A, V_{GS} = 0V$			1.2	V

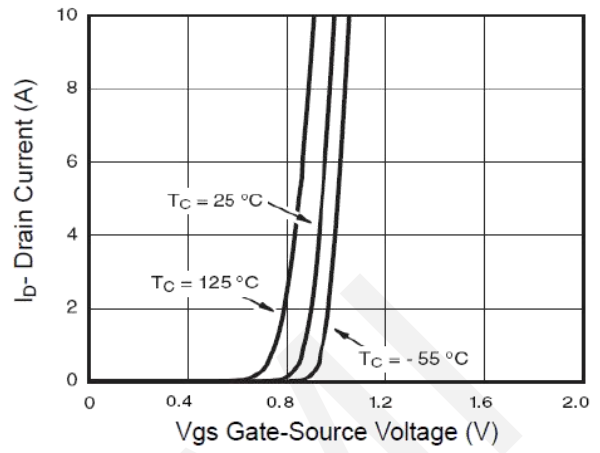
Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



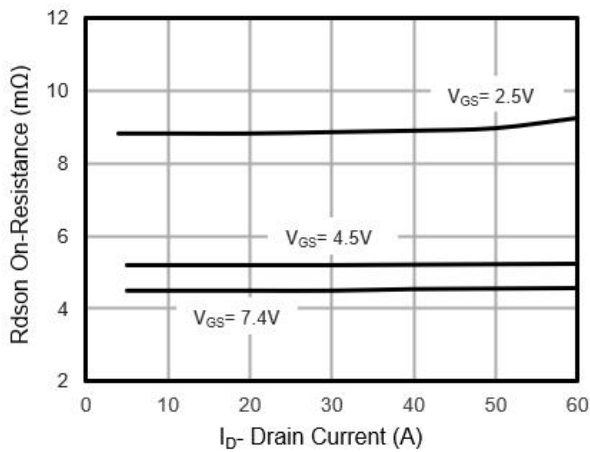
### 6. Typical electrical and thermal characteristics



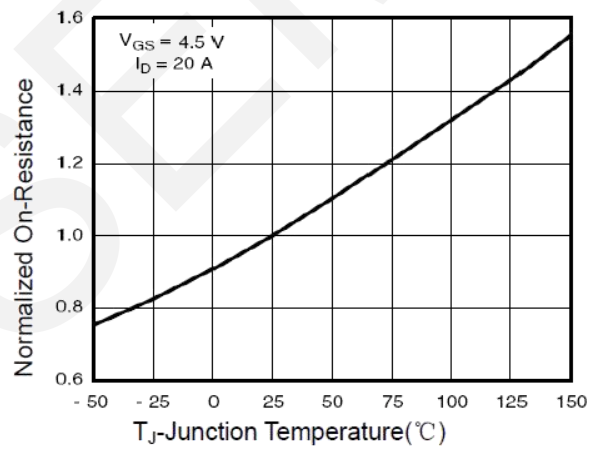
Output Characteristics



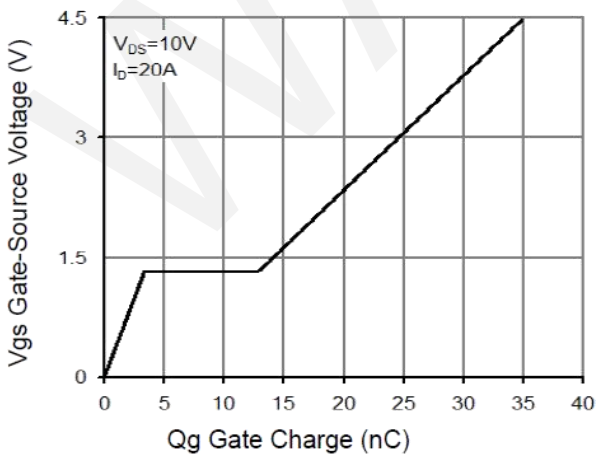
Transfer Characteristics



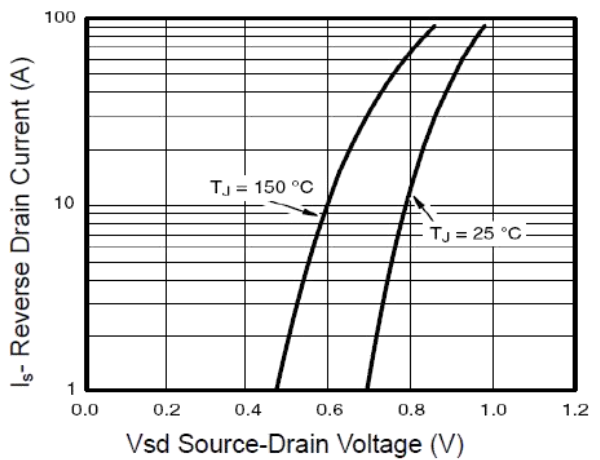
Rdson-Drain Current



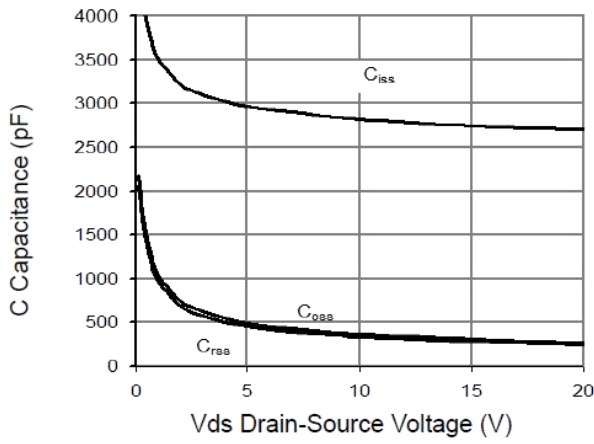
Rdson-Junction Temperature



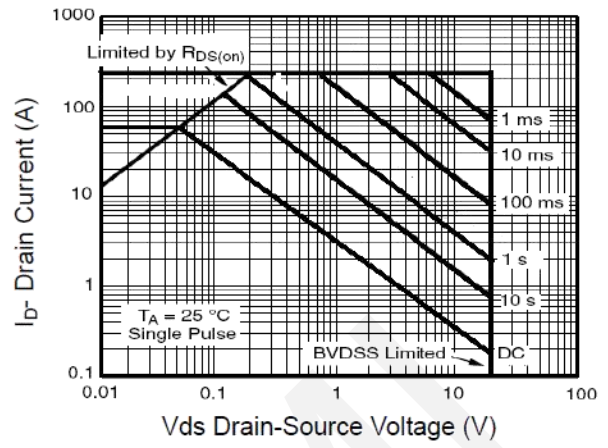
Gate Charge



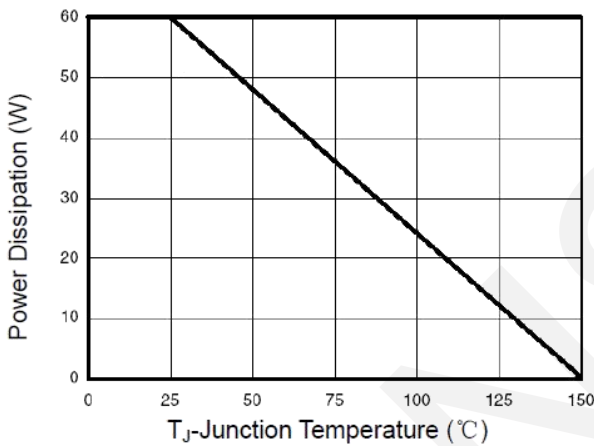
Source-Drain Diode Forward



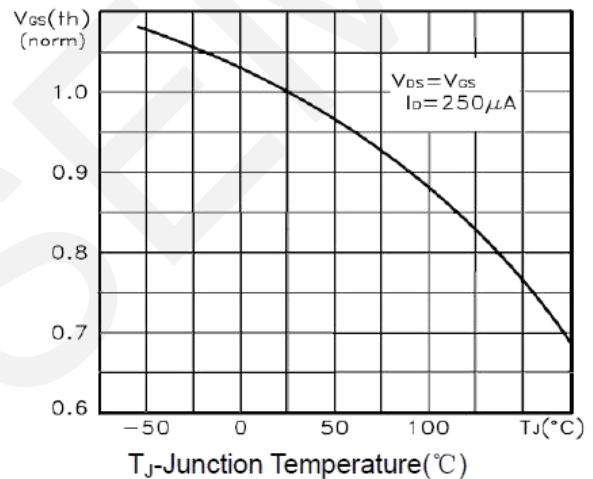
**Capacitance vs Vds**



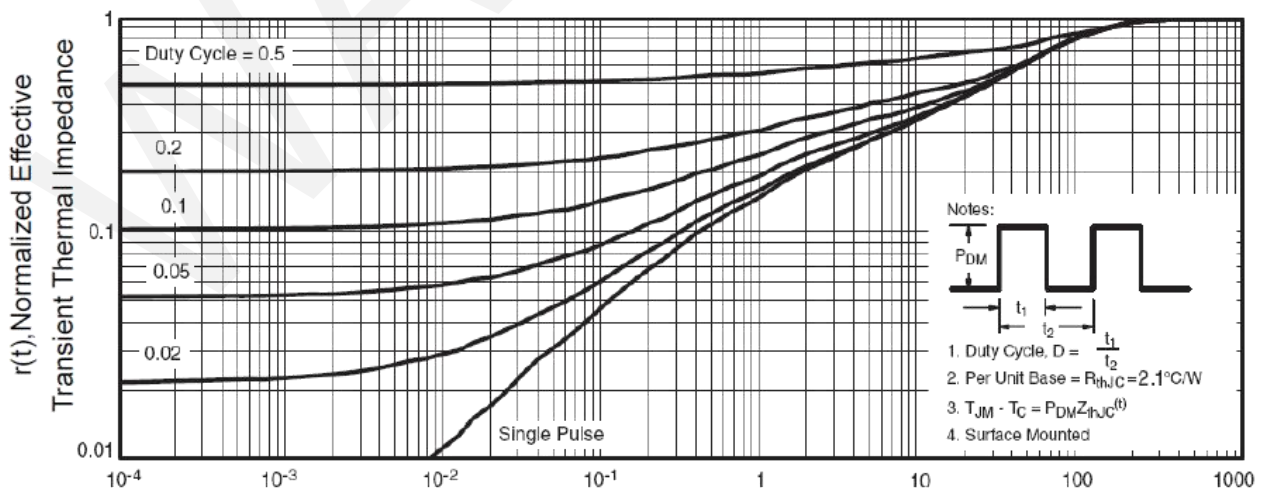
**Safe Operation Area**



**Power De-rating**



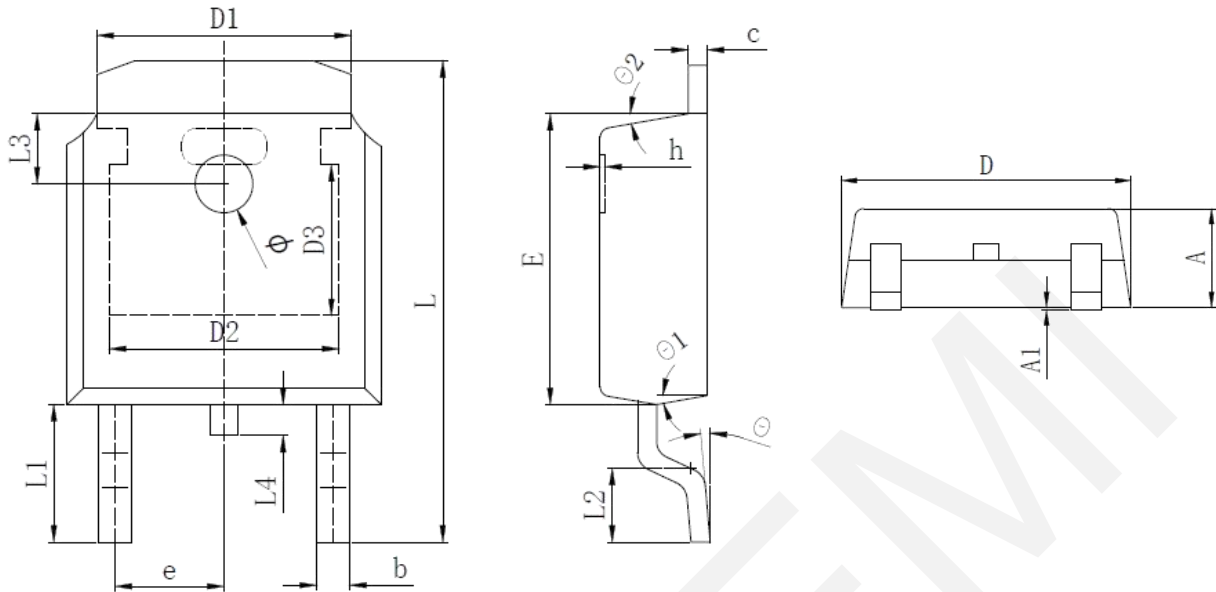
**$V_{GS(th)}$  vs Junction Temperature**



**Normalized Maximum Transient Thermal Impedance**



**7.Package Dimensions**



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c(电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
φ	1.100	1.200	1.300
θ	0°		8°
θ 1	9° TYP		
θ 2	9° TYP		

## 8. Important Notice

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